

FEATURES

Complimentary to SS8550

Marking : Y1

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current -Continuous	I_C	1500	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

SS8050 (NPN)


ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C=0.1mA, I_B=0$	25			V
Emitter-base breakdown voltage	V_{EBO}	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CB}	$V_{CB}=40V, I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CB}=20V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1V, I_C=100mA$	120		400	
	$h_{FE(2)}$	$V_{CE}=1V, I_C=800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=800mA, I_B=80mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=800mA, I_B=80mA$			1.2	V
Transition frequency	f_T	$V_{CE}=10V, I_C=50mA$ $f=30MHz$	100			MHz

 CLASSIFICATION OF h_{FE}

Rank	L	H	J
Range	120-200	200-350	300-400

SS8050 Typical Characteristics

